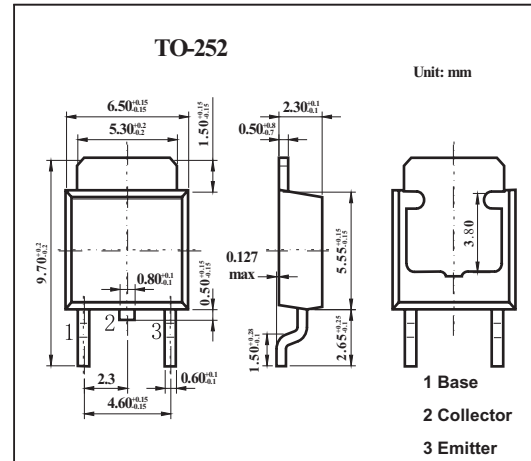


2SB906

■ Features

- Low collector saturation voltage.
- High power dissipation.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EB0}	-7	V
Collector current	I _C	-3	mA
Base current	I _B	-0.5	mA
Collector power dissipation	P _C	1	mW
Junction temperature	T _J	150	°C
Storage temperature range	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = -60 V, I _E = 0			-100	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -7 V, I _C = 0			-100	μA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -50mA, I _B = 0	-60			V
DC current gain	h _{FE}	V _{CE} = -5 V, I _C = -0.5 A	60		200	
		V _{CE} = -5 V, I _C = -3 A	20			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -3 A, I _B = -0.3 A		-1	-1.7	V
Base-emitter voltage	V _{BE}	V _{CE} = -5V, I _C = -0.5 A		-1	-1.5	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -0.5 A		9		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1 MHz		150		pF
Turn-on time	t _{on}	-I _{B1} =I _{B2} =0.2A, V _{CC} =-30V, duty cycle 1%		0.4		μs
Storage time	t _{stg}			1.7		μs
Fall time	t _f				0.5	

■ hFE Classification

Rank	O	Y
hFE	60~120	100~200